

## OptiMOS<sup>®</sup>-T Power-Transistor



### Product Summary

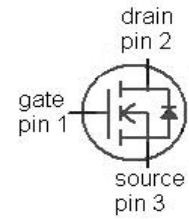
$V_{DS}$	120	V
$R_{DS(on),max}$ (SMD version)	11.8	m $\Omega$
$I_D$	70	A

### Features

- OptiMOS<sup>™</sup> - power MOSFET for automotive applications
- N-channel - Enhancement mode
- Automotive AEC Q101 qualified
- MSL1 up to 260°C peak reflow
- 175°C operating temperature
- Green product (RoHS compliant)
- 100% Avalanche tested



Type	Package	Marking
IPB70N12S3L-12	PG-TO263-3-2	3N12L12
IPI70N12S3L-12	PG-TO262-3-1	3N12L12
IPP70N12S3L-12	PG-TO220-3-1	3N12L12



Maximum ratings, at  $T_j=25\text{ °C}$ , unless otherwise specified

Parameter	Symbol	Conditions	Value	Unit
Continuous drain current	$I_D$	$T_C=25\text{ °C}$ , $V_{GS}=10\text{ V}$	70	A
		$T_C=100\text{ °C}$ , $V_{GS}=10\text{ V}^{1)}$	48	
Pulsed drain current <sup>1)</sup>	$I_{D,pulse}$	$T_C=25\text{ °C}$	280	
Avalanche energy, single pulse <sup>1)</sup>	$E_{AS}$	$I_D=35\text{ A}$	410	mJ
Avalanche current, single pulse	$I_{AS}$	-	70	A
Gate source voltage	$V_{GS}$	-	$\pm 20$	V
Power dissipation	$P_{tot}$	$T_C=25\text{ °C}$	125	W
Operating and storage temperature	$T_j, T_{stg}$	-	-55 ... +175	°C

Parameter	Symbol	Conditions	Values			Unit
			min.	typ.	max.	
<b>Thermal characteristics<sup>1)</sup></b>						
Thermal resistance, junction - case	$R_{thJC}$		-	-	1.2	K/W
Thermal resistance, junction - ambient, leaded	$R_{thJA}$		-	-	62	
SMD version, device on PCB	$R_{thJA}$	minimal footprint	-	-	62	
		6 cm <sup>2</sup> cooling area <sup>2)</sup>	-	-	40	

**Electrical characteristics, at  $T_j=25^\circ\text{C}$ , unless otherwise specified**

**Static characteristics**

Drain-source breakdown voltage	$V_{(BR)DSS}$	$V_{GS}=0\text{ V}, I_D=1\text{ mA}$	120	-	-	V
Gate threshold voltage	$V_{GS(th)}$	$V_{DS}=V_{GS}, I_D=83\mu\text{A}$	1.2	1.7	2.4	
Zero gate voltage drain current	$I_{DSS}$	$V_{DS}=120\text{V}, V_{GS}=0\text{V}, T_j=25^\circ\text{C}$	-	0.01	0.1	$\mu\text{A}$
		$V_{DS}=120\text{V}, V_{GS}=0\text{V}, T_j=125^\circ\text{C}^{2)}$	-	1	10	
Gate-source leakage current	$I_{GSS}$	$V_{GS}=20\text{V}, V_{DS}=0\text{V}$	-	-	100	nA
Drain-source on-state resistance	$R_{DS(on)}$	$V_{GS}=4.5\text{V}, I_D=70\text{A}$	-	12.2	15.8	m $\Omega$
		$V_{GS}=4.5\text{V}, I_D=70\text{A},$ SMD version	-	11.9	15.5	
		$V_{GS}=10\text{ V}, I_D=70\text{ A}$	-	10.1	12.1	
		$V_{GS}=10\text{ V}, I_D=70\text{ A},$ SMD version	-	9.8	11.8	

Parameter	Symbol	Conditions	Values			Unit
			min.	typ.	max.	

### Dynamic characteristics<sup>1)</sup>

Input capacitance	$C_{iss}$	$V_{GS}=0V, V_{DS}=25V,$ $f=1MHz$	-	4270	5550	pF
Output capacitance	$C_{oss}$		-	950	1230	
Reverse transfer capacitance	$C_{rss}$		-	90	135	
Turn-on delay time	$t_{d(on)}$	$V_{DD}=20V, V_{GS}=10V,$ $I_D=50A, R_G=3.5\Omega$	-	10	-	ns
Rise time	$t_r$		-	5	-	
Turn-off delay time	$t_{d(off)}$		-	28	-	
Fall time	$t_f$		-	5	-	

### Gate Charge Characteristics<sup>1)</sup>

Gate to source charge	$Q_{gs}$	$V_{DD}=96V, I_D=70A,$ $V_{GS}=0\text{ to }10V$	-	15	21	nC
Gate to drain charge	$Q_{gd}$		-	11	17	
Gate charge total	$Q_g$		-	59	77	
Gate plateau voltage	$V_{plateau}$		-	3.5	-	V

### Reverse Diode

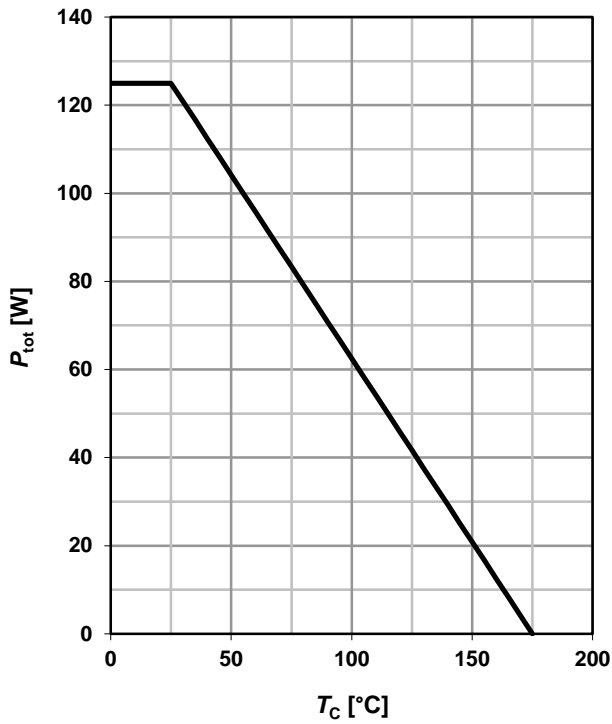
Diode continuous forward current <sup>1)</sup>	$I_S$	$T_C=25^\circ C$	-	-	70	A
Diode pulse current <sup>1)</sup>	$I_{S,pulse}$		-	-	280	
Diode forward voltage	$V_{SD}$	$V_{GS}=0V, I_F=70A,$ $T_j=25^\circ C$	0.6	1	1.2	V
Reverse recovery time <sup>1)</sup>	$t_{rr}$	$V_R=60V, I_F=50A,$ $di_F/dt=100A/\mu s$	-	80	-	ns
Reverse recovery charge <sup>1)</sup>	$Q_{rr}$		-	185	-	

<sup>1)</sup> Defined by design. Not subject to production test.

<sup>2)</sup> Device on 40 mm x 40 mm x 1.5 mm epoxy PCB FR4 with 6 cm<sup>2</sup> (one layer, 70 μm thick) copper area for drain connection. PCB is vertical in still air.

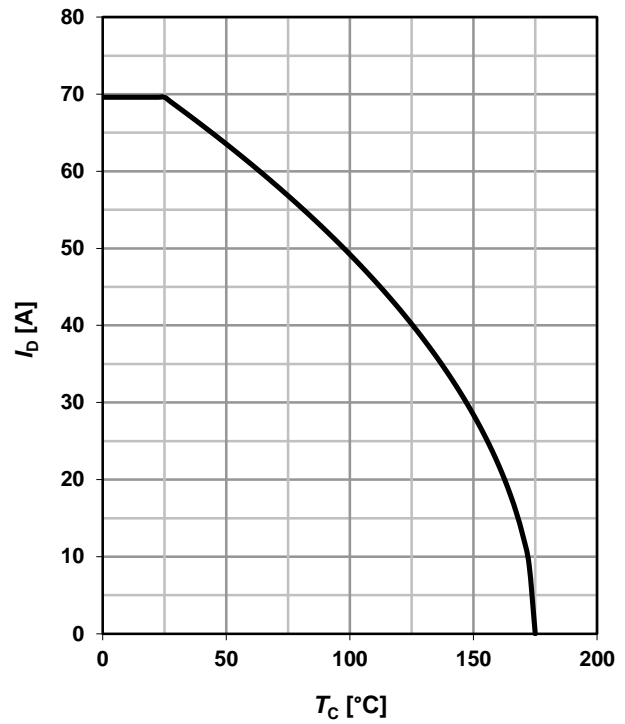
**1 Power dissipation**

$P_{tot} = f(T_C); V_{GS} = 10\text{ V}$



**2 Drain current**

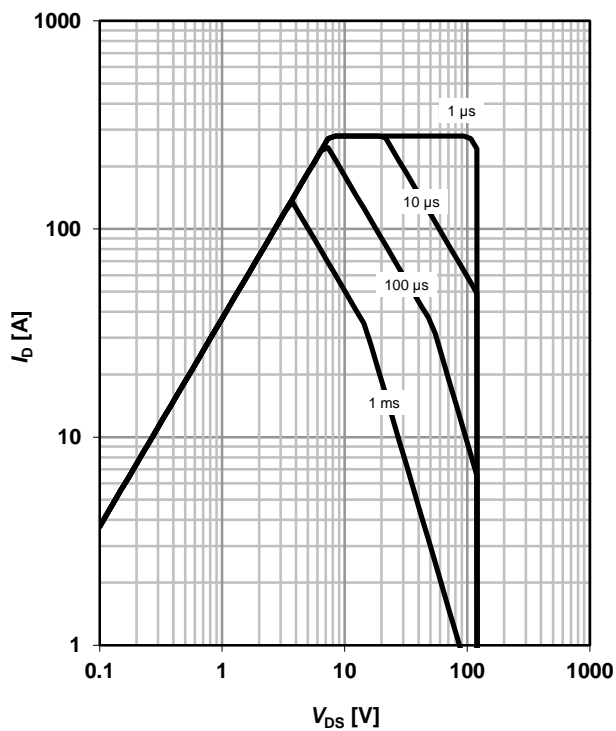
$I_D = f(T_C); V_{GS} = 10\text{ V}; \text{SMD}$



**3 Safe operating area**

$I_D = f(V_{DS}); T_C = 25\text{ °C}; D = 0; \text{SMD}$

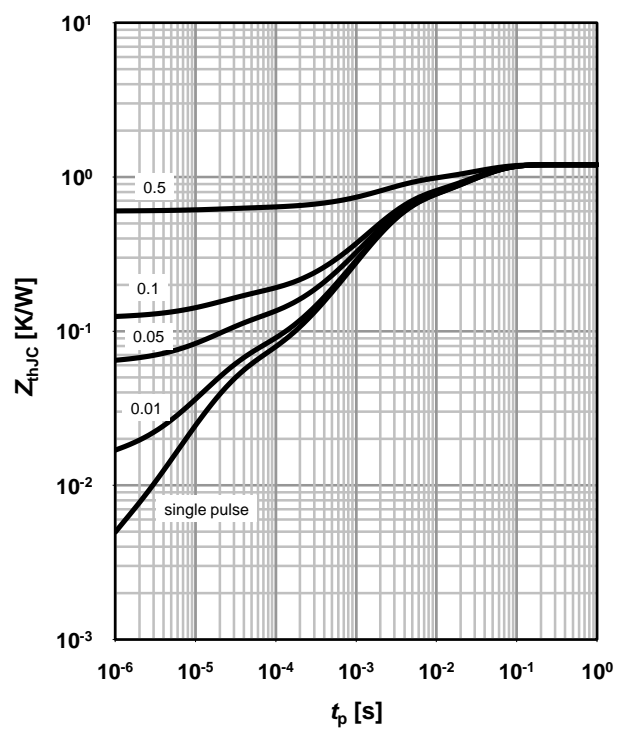
parameter:  $t_p$



**4 Max. transient thermal impedance**

$Z_{thJC} = f(t_p)$

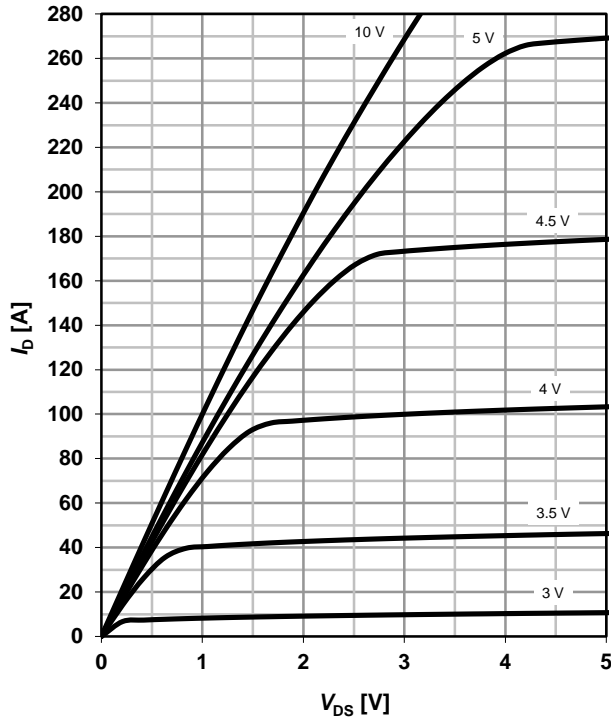
parameter:  $D = t_p/T$



**5 Typ. output characteristics**

$I_D = f(V_{DS}); T_j = 25\text{ }^\circ\text{C}; \text{SMD}$

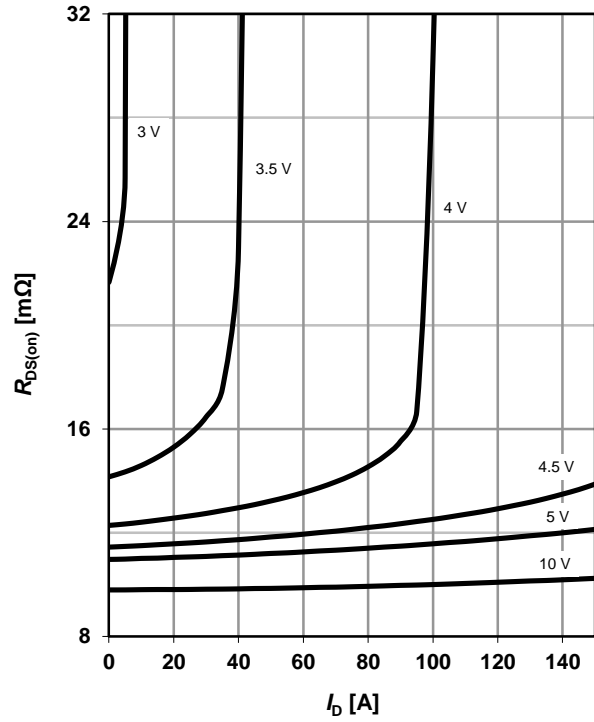
parameter:  $V_{GS}$



**6 Typ. drain-source on-state resistance**

$R_{DS(on)} = f(I_D); T_j = 25\text{ }^\circ\text{C}; \text{SMD}$

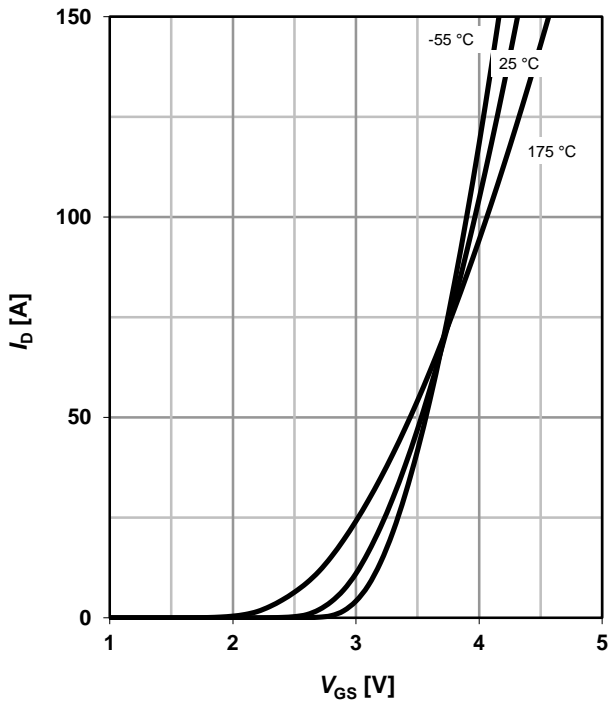
parameter:  $V_{GS}$



**7 Typ. transfer characteristics**

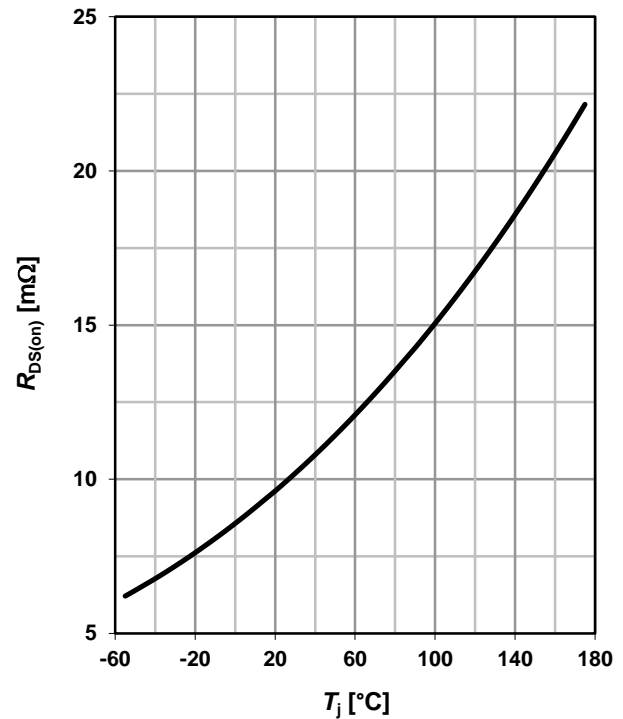
$I_D = f(V_{GS}); V_{DS} = 6\text{ V}$

parameter:  $T_j$



**8 Typ. drain-source on-state resistance**

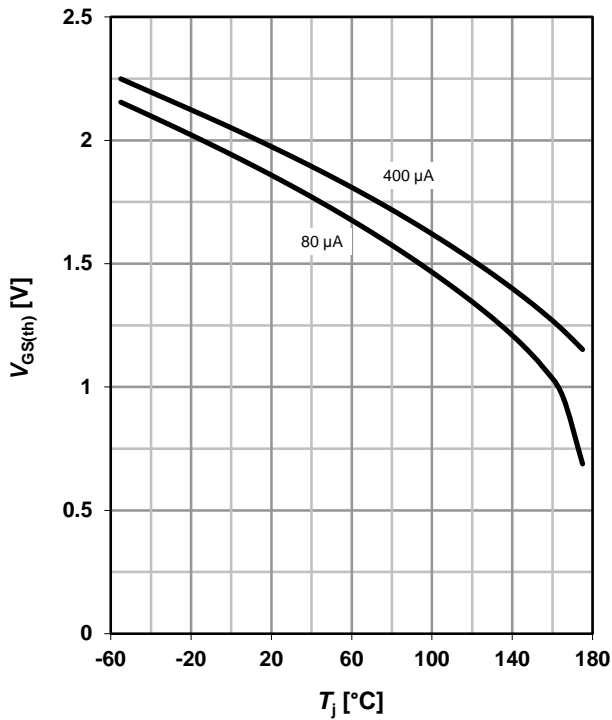
$R_{DS(on)} = f(T_j); I_D = 50\text{ A}; V_{GS} = 10\text{ V}; \text{SMD}$



**9 Typ. gate threshold voltage**

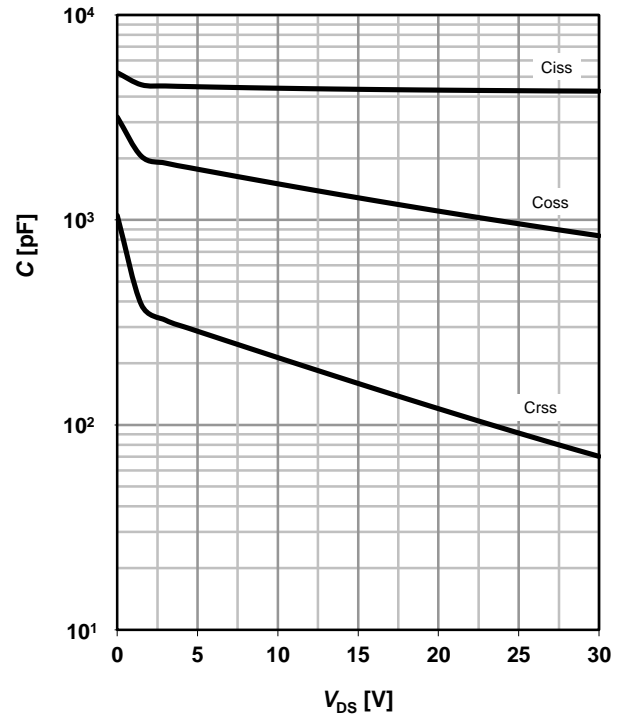
$V_{GS(th)} = f(T_j); V_{GS} = V_{DS}$

parameter:  $I_D$



**10 Typ. capacitances**

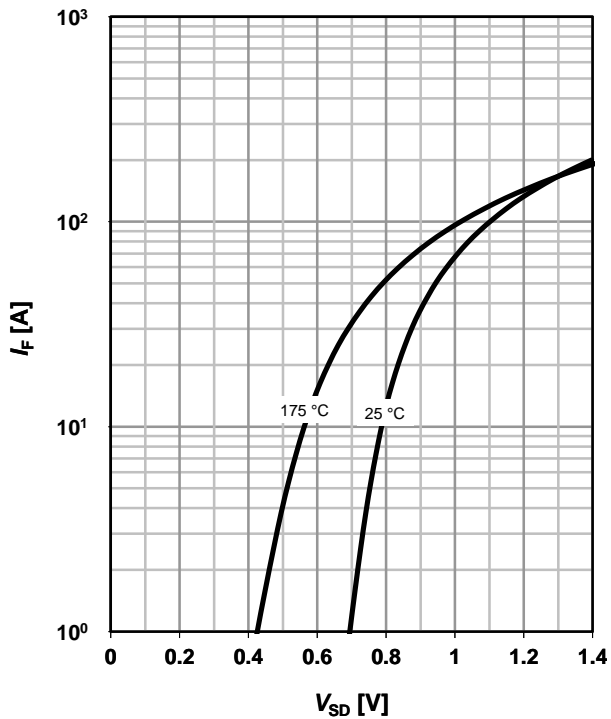
$C = f(V_{DS}); V_{GS} = 0 \text{ V}; f = 1 \text{ MHz}$



**11 Typical forward diode characteristics**

$I_F = f(V_{SD})$

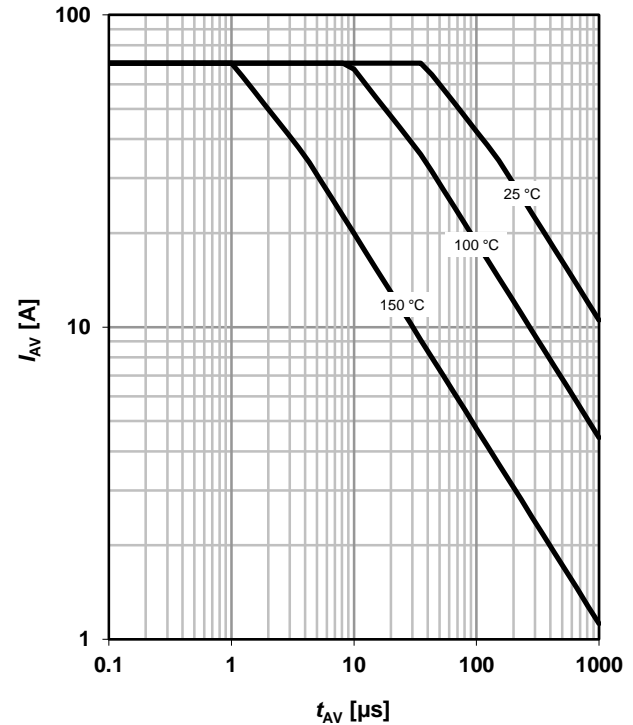
parameter:  $T_j$



**12 Typ. avalanche characteristics**

$I_{AS} = f(t_{AV})$

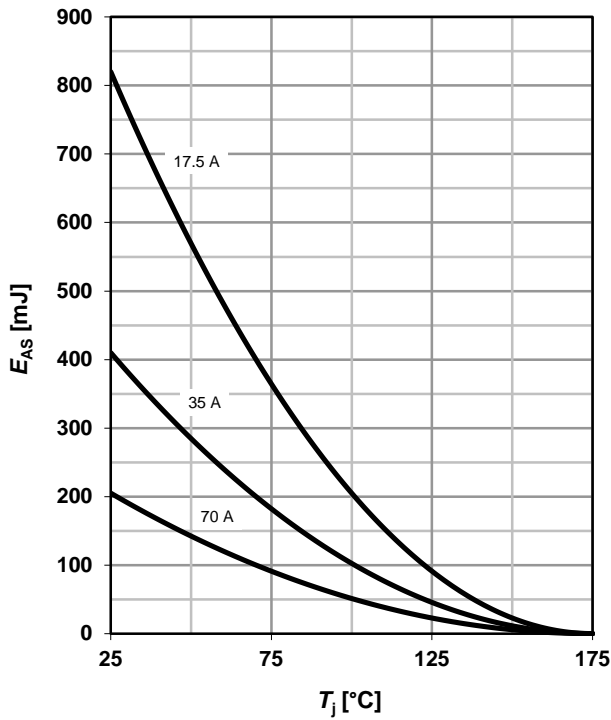
parameter:  $T_{j(start)}$



**13 Typical avalanche energy**

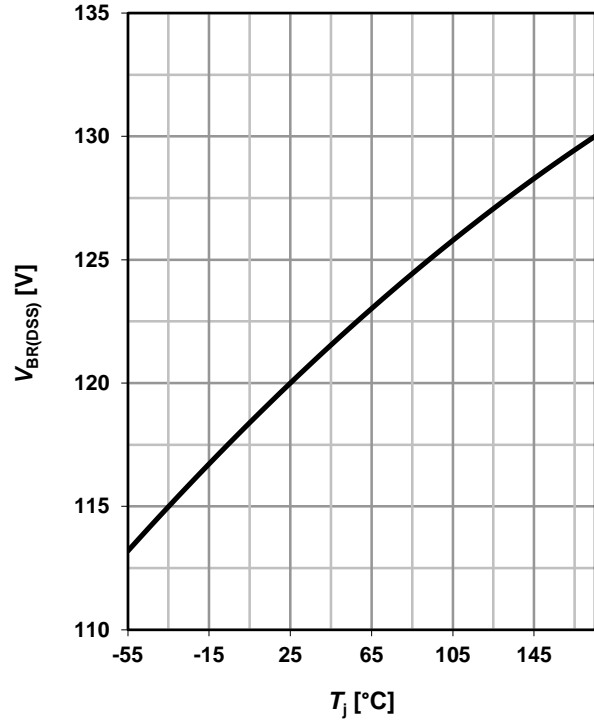
$$E_{AS} = f(T_j)$$

parameter:  $I_D$



**14 Typ. drain-source breakdown voltage**

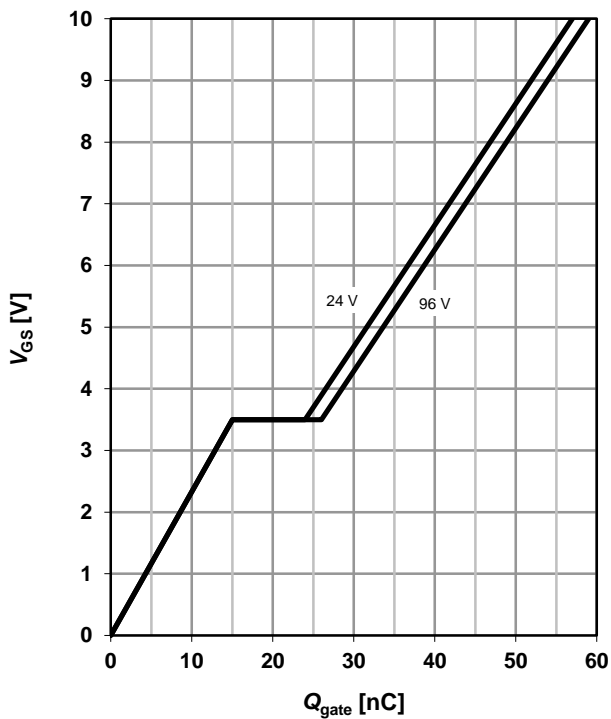
$$V_{BR(DSS)} = f(T_j); I_D = 1 \text{ mA}$$



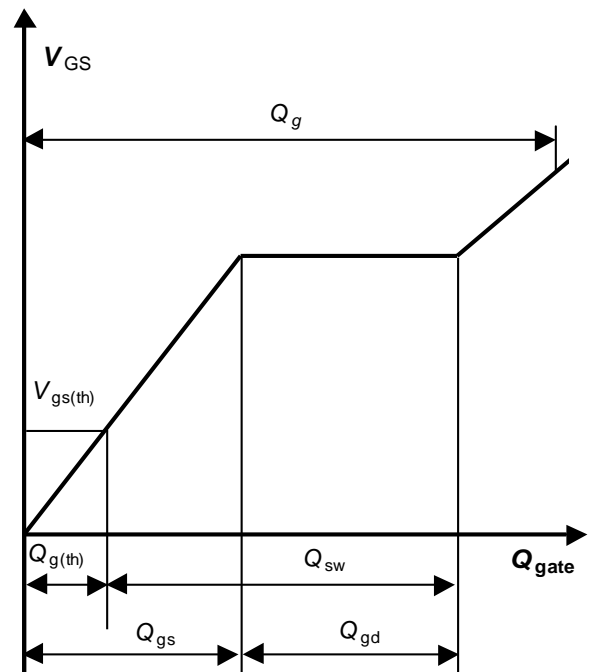
**15 Typ. gate charge**

$$V_{GS} = f(Q_{gate}); I_D = 70 \text{ A pulsed}$$

parameter:  $V_{DD}$



**16 Gate charge waveforms**



**Published by**  
**Infineon Technologies AG**  
**81726 Munich, Germany**

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Revision History

Version	Date	Changes
Revision 1.0	20.06.2016	Final Data Sheet

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